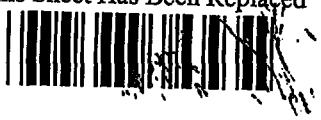
ABSTRACT OF THE DISCLOSURE

A process for producing a semiconductor substrate is provided which comprises providing a first substrate made of silicon having a porous silicon layer formed thereon by making porous the substrate silicon and a nonporous monocrystalline silicon layer epitaxially grown on the porous silicon layer, laminating the first substrate onto a second substrate in a state that at least one of lamination faces of the first and the second substrates has a silicon oxide layer and the nonporous monocrystalline silicon layer is interposed between the laminated substrates, and removing the porous silicon layer by etching, wherein the porous silicon layer is removed by etching with an etchant which etches the nonporous monocrystalline silicon layer and the silicon oxide layer at respective etching rates of not more than 10 angstroms per minute.

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